

IPW50R399CPFKSA1

IPW50R399CPFKSA1 Information



For Reference Only

Part Number IPW50R399CPFKSA1 **Manufacturer** Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 560V 9A TO-247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IPW50R399CPFKSA1 Specifications

Manufacturer Part Number IPW50R399CPFKSA1 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series CoolMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 560V Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 330µA Gate Charge (Qg) (Max) @ Vgs 23nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 890pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 83W (Tc) Rds On (Max) @ Id, Vgs 399 mOhm @ 4.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-T0247-3 Package / Case TO-247-3 Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-247-3 Series CoolMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Train to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 10put Capacitance (Ciss) (Max) @ Vds 890pF @ 100V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 399 mOhm @ 4.9A, 10V Operating Temperature Mounting Type Supplier Device Package PG-TO247-3 Package / Case TO-247-3	Manufacturer Part Number	IPW50R399CPFKSA1
Package TO-247-3 Series CoolMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 560V Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 330μA Gate Charge (Qg) (Max) @ Vgs 23nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 890pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 83W (Tc) Rds On (Max) @ Id, Vgs 399 mOhm @ 4.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case TO-247-3	Manufacturer	Infineon Technologies
Package TO-247-3 Series CoolMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 560V Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 330μA Gate Charge (Qg) (Max) @ Vgs 23nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 890pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 83W (Tc) Rds On (Max) @ Id, Vgs 399 mOhm @ 4.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case TO-247-3	Category	Discrete Semiconductor Products
Series CoolMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 560V Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 330μA Gate Charge (Qg) (Max) @ Vgs 23nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 890pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 83W (Tc) Rds On (Max) @ Id, Vgs 399 mOhm @ 4.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case TO-247-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 560V Current - Continuous Drain (Id) @ 25°C 9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 330µA Gate Charge (Qg) (Max) @ Vgs 23nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 890pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 83W (Tc) Rds On (Max) @ Id, Vgs 399 mOhm @ 4.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case Toolean Since (Since And Source (Since And Sour	Package	TO-247-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package PG-TO247-3 Package / Case MOSFET (Metal Oxide) MOSFET (Metal Oxide) 560V 560V 9A (Tc) 9A (To) 9A (Tc)	Series	CoolMOS?
Drain to Source Voltage (Vdss)560VCurrent - Continuous Drain (Id) @ 25°C9A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 330μAGate Charge (Qg) (Max) @ Vgs23nC @ 10VInput Capacitance (Ciss) (Max) @ Vds890pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)83W (Tc)Rds On (Max) @ Id, Vgs399 mOhm @ 4.9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO247-3Package / CaseTO-247-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case PASS On (Max Rds On, Min Rds On) 10V 9A (Tc) 9A	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 330μAGate Charge (Qg) (Max) @ Vgs23nC @ 10VInput Capacitance (Ciss) (Max) @ Vds890pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)83W (Tc)Rds On (Max) @ Id, Vgs399 mOhm @ 4.9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO247-3Package / CaseTO-247-3	Drain to Source Voltage (Vdss)	560V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 890pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 399 mOhm @ 4.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case TO-247-3	Current - Continuous Drain (Id) @ 25°C	9A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 890pF @ 100V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 399 mOhm @ 4.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 399 mOhm @ 4.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case TO-247-3	Vgs(th) (Max) @ Id	3.5V @ 330µA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)83W (Tc)Rds On (Max) @ Id, Vgs399 mOhm @ 4.9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO247-3Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	23nC @ 10V
FET Feature - Power Dissipation (Max) 83W (Tc) Rds On (Max) @ Id, Vgs 399 mOhm @ 4.9A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	890pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case 83W (Tc) 399 mOhm @ 4.9A, 10V -55°C ~ 150°C (TJ) Through Hole Through Hole	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs399 mOhm @ 4.9A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO247-3Package / CaseTO-247-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case TO-247-3	Power Dissipation (Max)	83W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO247-3 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	399 mOhm @ 4.9A, 10V
Supplier Device Package PG-TO247-3 Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
-	Supplier Device Package	PG-TO247-3
Report errors?	Package / Case	TO-247-3
		Report errors?

IPW50R399CPFKSA1 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPW50R399CPFKSA1 Payment Methods



















IPW50R399CPFKSA1 Shipping Methods













If you have any question about IPW50R399CPFKSA1, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com